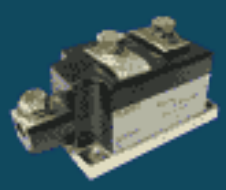
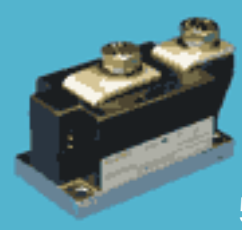
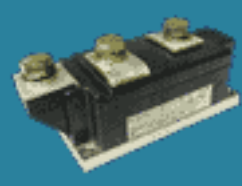
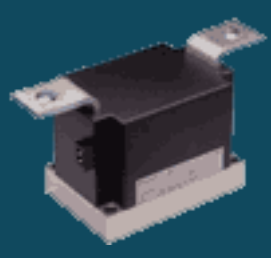
the figures in the part-no. represent the current rating [A]

part-no.	$V_{RRM, DRM}$	PowerBLOCK
TT 61 N TD/DT 61 N	1200...1600V	 20 mm
TT 92 N TD/DT 92 N	1000...1600V	
TT 104 N TD/DT 104 N	1000...1400V	
TT 70 N TD 70 N	1600...2400V	 25 mm
TT 85 N TD/DT 85 N	2000V	
TT 106 N TD/DT 106 N	1000...1800V	
TT 121 N TD/DT 121 N	1200...2000V	 30 mm
TT 131 N TD/DT 131 N	1200...1600V	
TT 122 N TD 122 N	1600...2400V	 34 mm
TT 140 N.	1600...2200V	
TT 142 N TD/DT 142 N	1200...1600V	
TT 162 N TD/DT 162 N	1200...1600V	
TT 180 N	1200...1600V	
TT 150 N TD/DT 150 N	1800...2600V	 50 mm
TT 170 N TD/DT 170 N	1000...1800V	
TT 210 N TD/DT 210 N	1000...1800V	
TT 215 N TD 215 N	1800...2400V	
TT 250 N TD/DT 250 N	1000...1800V	
TT 251 N TD/DT 251 N	1000...1800V	
TT 265 N	200...600V	
TT 285 N TD/DT 285 N	1200...1600V	
TT 330 N	1200...1600V	

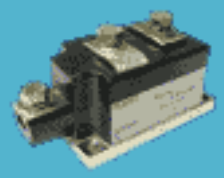
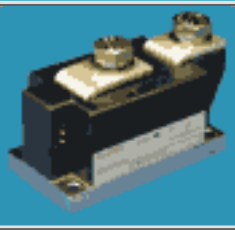
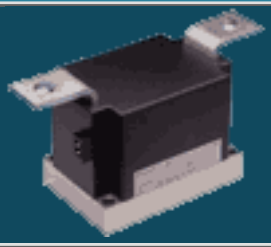
part-no.	$V_{RRM, DRM}$	PowerBLOCK
TZ 150 N	1800...2600V	 50 mm
TZ 240 N	2800...3600V	
TZ 310 N	2000...2600V	
TZ 400 N	2000...2600V	
TZ 425 N	1000...1800V	
TZ 430 N	1800...2400V	
TZ 500 N	1000...1800V	
TZ 600 N	1000...1400V	
TT 240 N TD 240 N	2800...3600V	 60 mm
TT 310 N TD/DT 310 N	2000...2600V	
TT 380 N.	1000...1800V	
TT 400 N.	2000...2600V	
TT 425 N TD/DT 425 N	1000...1800V	
TT 430 N.	1800...2400V	
TT 500 N TD/DT 500 N	1000...1800V	
TT 570 N	1200...1600V	
TZ 530 N	3000...3600V	 70 mm
TZ 630 N	2200...2800V	
TZ 740 N	1800...2200V	
TZ 800 N	1200...1800V	

Common anode or cathode on request

click on part-no. to select datasheet - click on other topologies to change menu

the figures in the part-no. represent the current rating [A]

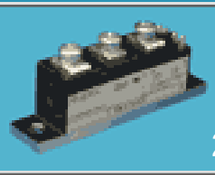
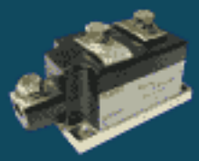
part-no.	$V_{RRM, DRM}$	PowerBLOCK
DD 85 N	800...1600V	 20 mm
DD 89 N	1000...1800V	
DD 98 N	2000...2500V	
DD 104 N ND 104 N	1000...1800V	
DD 106 N	1200...2200V	 25 mm
DD 151 N	1200...2000V	 30 mm
DD 171 N ND 171 N	1200...1800V	 34 mm

part-no.	$V_{RRM, DRM}$	PowerBLOCK
DD 175 N	2800...3400V	 50 mm
DD 231 N	2000...2600V	
DD 260 N ND 260 N	1000...1800V	
DD 261 N	2000...2600V	
DD 285 N	400...800V	
DD 350 N	1000...1800V	
DZ 540 N	2000...2600V	 50 mm
DZ 600 N	1200...1800V	
DD 435 N	2800...4000V	 60 mm
DD 540 N	2000...2600V	
DD 600 N ND 600 N	1200...1800V	
DZ 950 N	3600...4400V	 70 mm
DZ 1070 N	1800...2800V	

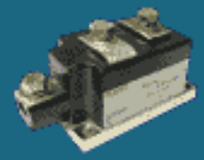
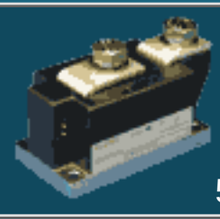
click on part-no. to select datasheet - click on other topologies to change menu

the figures in the part-no. represent the current rating [A]

Fast Thyristor Modules

part-no.	$V_{RRM, DRM}$	PowerBLOCK
TT 46 F TD 46 F	800...1200V	 20 mm
TT 71 F TD/DT 71 F	1000...1400V	 30 mm
TT 81 F TD/DT 81 F	400...800V	
TT 101 F TD/DT 101 F	1000...1400V	
TT 111 F TD/DT 111 F	800...1000V	
TT 180 F TD/DT 180 F	1000...1300V	 50 mm
TT 200 F TD/DT 200 F	1000...1300V	
TZ 335 F	1000...1300V	

Fast Diode Modules

part-no.	$V_{RRM, DRM}$	PowerBLOCK
DD 46 S	800...1200V	 20 mm
DD 61 S	1000...1400V	
DD 62 S	400...1000V	
DD 81 S	1000...1400V	
DD 82 S	400...1000V	
DD 121 S	1000...1400V	 30 mm
DD 122 S	400...1000V	
DD 230 S ND 230 S	1800...2600V	 50 mm
DD 241 S ND 241 S	1000...1400V	
DD 242 S ND 242 S	600...1000V	
DZ 180 S *)	2500V	 50 mm
DZ 180 U *)	2500V	

*) base plate not electrically isolated

click on part-no. to select datasheet - click on other topologies to change menu

Type designations

Thyristors

T 930 S 18 T M C

T		symmetrically blocking thyristor
A		asymmetrically blocking thyristor
930		limiting average forward current (A) at tc= 85° C
0		Ceramic disc W
1		Ceramic disc P
4		Epoxy disc 19 mm high
6		Epoxy disc 35 mm high
7		Epoxy disc 8 mm high
8		Epoxy disc 14 mm high
9		Epoxy disc 26 mm high
2.Letter		
S		fast thyristor, gate-cathode interdigitated
F		fast thyristor, central gate
N		phase control thyristor
18		limiting repetitive peak forward and reverse off-state voltage in 100 V, 18 = 1800 V (A: repetitive peak forward off-state voltage)
3.Letter		mechanical construction anode: cathode:
B		metric thread cable
C		metric thread solder pin
E		flat base cable
F		TO 220 case
T		disc
4.Letter		maximum turn-off time
A		8 µs
B		10 µs
C		12 µs
D		15 µs
S		18 µs
E		20 µs
F		25 µs
G		30 µs
K		40 µs
M		50 µs
P		55 µs
N		60 µs
T		80 µs
U		120 µs
O		no guaranteed max. value
1		see data sheet
2		see data sheet
5.Letter		critical rate of rise forward voltage, thyristors for line commutated converters:
B		50 V/µs
C		500 V/µs
F		1000 V/µs
G		1500 V/µs
H		2000 V/µs
		thyristors for self-commutated converters: critical rate of rise of forward voltage according to DIN IEC 747-6: / immediately after turn-off:
B		50 V/µs / 50 V/µs
C		500 V/µs / 500 V/µs
F		1000 V/µs / 1000 V/µs
L		500 V/µs / 50 V/µs
M		1000 V/µs / 500 V/µs
N		1000 V/µs / 50 V/µs

Rectifier diodes

D 1809 N 32

D		diode
1809		limiting average current (A) as a rule at tc = 100° C
N		rectifier diode: anode on case or press-pack
K		cathode on case
		fast rectifier diode:
S		anode on case or press-pack
U		cathode on case
32		limiting repetitive peak reverse voltage in 100 V
		mechanical construction:
A		metric thread wire
B		metric thread cable
C		stud solder pin
E		flat-base cable
T		press-pack
A		Avalanche Diode anode / case
B		Avalanche Diode cathode / case

Half-controlled thyristor modules

TD 121 N 18 K O F -A

TD,DT		with 1 symmetric thyristor and 1 diode
AD		with 1 asymmetric thyristor and 1 diode (for circuit see outline)
121		limiting average on-state current (A), tc = 85° C
N		phase control thyristor and retifier diode
F		fast thyristor and fast diode
S		fast thyristor with interdigitated gate and fast diode
18		repetitive peak-off-state voltage in 100 V
K		mech. constr.: pressure contact
O		turn-off time (see thyristors)
F		critical rate of rise of off-state voltage
-A		special design with common anode
-K		special design with common cathode

Fully controlled Thyristor modules

TT 121 N 18 K O F -A

TT		with 2 symmetric thyristors
TZ		with 1 symmetric thyristor
121		limiting average on-state current (A), tc = 85° C
N		phase control thyristor
F		fast thyristor with central gate
18		repetitive peak off-state voltage in 100 V
L		mech. constr.: module-DCB
K		mech. constr.: module
O		turn-off time (see thyristors)
F		critical rate of rise of off-state voltage
-A		special design with common anode
-K		special design with common cathode

Diode modules

DD 151 N 18 K -A

DD		dual version
D, ND, DZ		with 1 diode (for circuit see outline)
151		limiting average forward current (A), tc = 100° C
N		rectifier diode
S		fast rectifier diode
18		repetitive peak off-state voltage in 100 V
L		mech. constr.: module-DCB
K		mech. constr.: module
-A		special design with common anode
-K		special design with common cathode

Bridge Rectifiers and AC-Switches

TD B6 HK 105 N 16 KOF

DD		diode module
TT		thyristor module
TD		thyristor/diode
B6		three phase bridge
W3		three phase AC-switch
C		fully controlled
H		half controlled
U		uncontrolled
K		common cathode of thyristors
105		output current (A) (W3C: RMS-current)
N		phase control thyristor/diode
16		repetitive peak off-state voltage in 100V
L		mech. constr.: module
R		outline: ECONOPACK
RR		outline: ECONOPACK with integr. brake chopper IGBT
O		no guaranteed turn-off time
F		critical rate of rise of off-state voltage

IGBT modules Type designation

IGBT & Diode: IHM/IHV & all new eupec modules

FF 800 R 17 K F 6 D B2

FF		Dual Switch
FZ		Single Switch
FS		3-phase full Bridge
FP		Power integrated Modul
F4-		One phase bridge
FD		Chopper config.
DD		Dual Diode (for circuit see outline)
800		Max. DC-collector current (A)
R		Reverse conducting
S		Fast Short Tail IGBT Chip
17		Collector-emitter-voltage in 100 V
K		Mechanical construction: Module
F		Fast switching IGBT Chip
L		Low Loss IGBT Chip
S		Fast Short Tail IGBT Chip
E		Low Sat & fast IGBT^3 Chip
1..n		Internal reference number
C		With EmCon diode
D		Higher rated diode
B1..n		Construction variation
S1..n		Electrical selection

IGBT & Diodes: BSM modules

BSM 100 GB 120 D N2 K

B		Silicon
S		Type: S=Switch, Y = Diode
M		Module
100		current rating I_C = 100 A
G		technology: G = IGBT-technology
B		Configuration: A = single switch / diode, B = Halfbridge, D = 3-phase full bridge, T = Tripack (3 single switches), P = Power Integrated Module, AL=Chopper, diode conn. to collector, AR=Chopper, diode conn. to emitter
120		max. coll.-emitter-voltage in 10V
D		with fast internal diode
N		low inductance module design
L		Low Loss IGBT chip
2		2nd generation silicon
		K design variation
		G design variation
		S collector sense
		E xxxx special type with code-no.